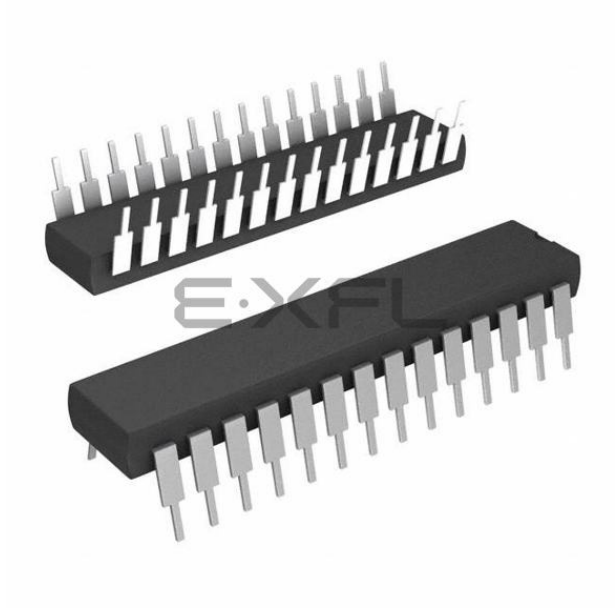


Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	PIC
Core Size	8-Bit
Speed	64MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, HLVD, POR, PWM, WDT
Number of I/O	24
Program Memory Size	64KB (32K x 16)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	3.8K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 11x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Through Hole
Package / Case	28-DIP (0.300", 7.62mm)
Supplier Device Package	28-SPDIP
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic18f26k20-i-sp

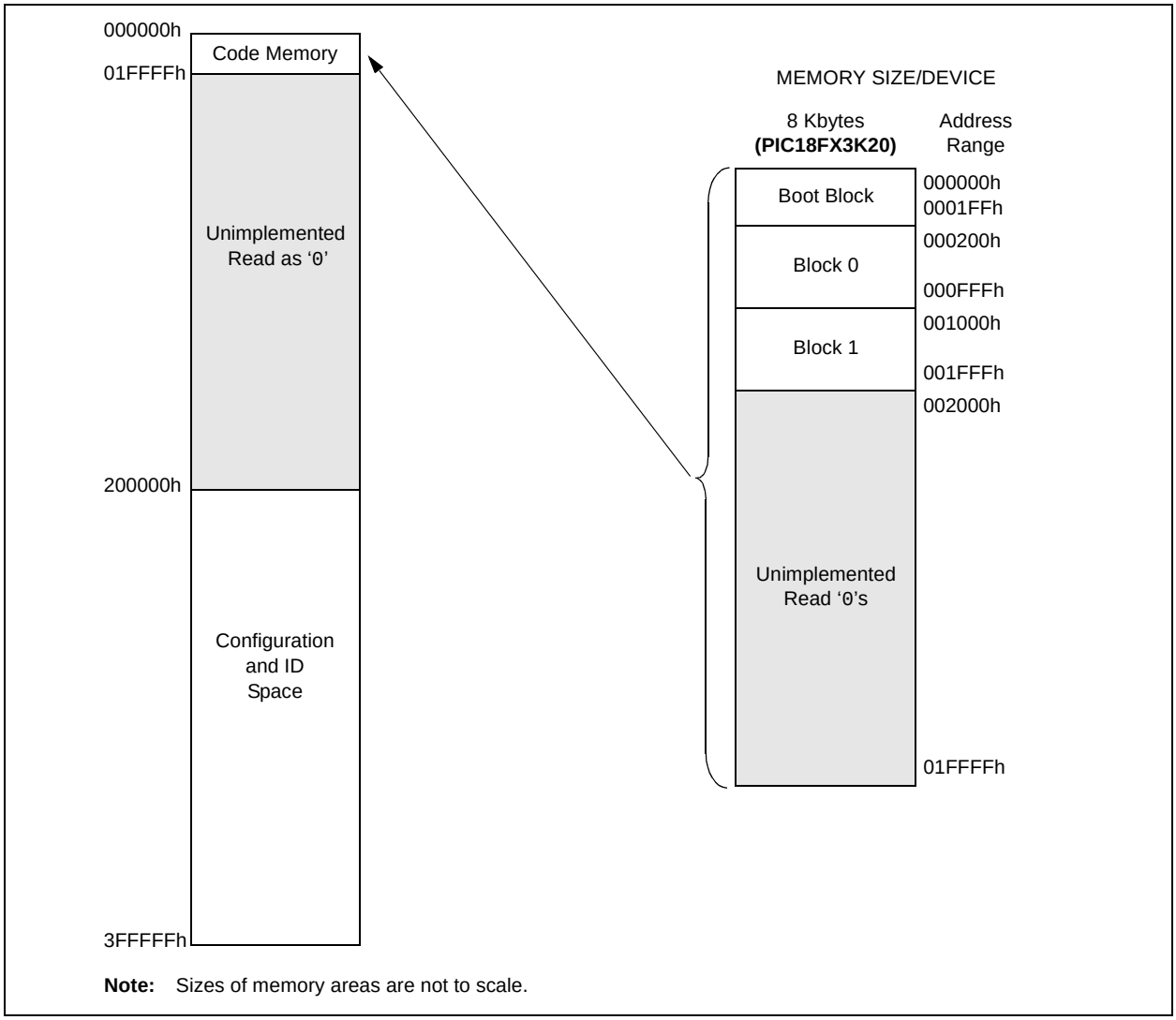
2.3 Memory Maps

For the PIC18FX3K20 devices, the code memory space extends from 0000h to 01FFFh (8 Kbytes) in two 4-Kbyte blocks. Addresses 0000h through 01FFh, however, define a “Boot Block” region that is treated separately from Block 0. All of these blocks define code protection boundaries within the code memory space.

TABLE 2-2: IMPLEMENTATION OF CODE MEMORY

Device	Code Memory Size (Bytes)
PIC18F23K20	000000h-001FFFh (8K)
PIC18F43K20	

FIGURE 2-6: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18FX3K20 DEVICES



Note: Sizes of memory areas are not to scale.

In addition to the code memory space, there are three blocks in the configuration and ID space that are accessible to the user through table reads and table writes. Their locations in the memory map are shown in Figure 2-10.

Users may store identification information (ID) in eight ID registers. These ID registers are mapped in addresses 200000h through 200007h. The ID locations read out normally, even after code protection is applied.

Locations 300000h through 30000Dh are reserved for the Configuration bits. These bits select various device options and are described in **Section 5.0 "Configuration Word"**. These Configuration bits read out normally, even after code protection.

Locations 3FFFFEh and 3FFFFFh are reserved for the device ID bits. These bits may be used by the programmer to identify what device type is being programmed and are described in **Section 5.0 "Configuration Word"**. These device ID bits read out normally, even after code protection.

2.3.1 MEMORY ADDRESS POINTER

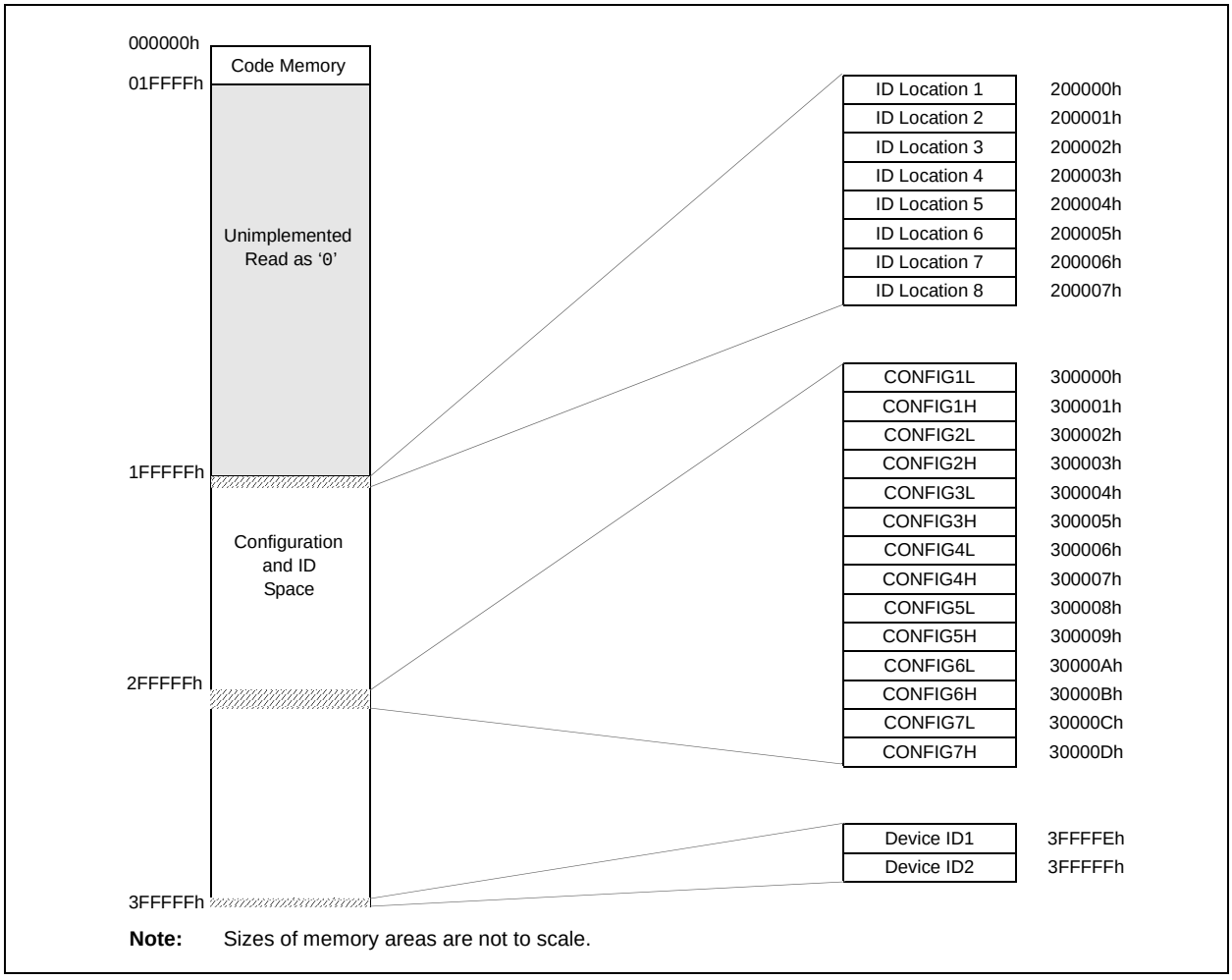
Memory in the address space, 0000000h to 3FFFFFh, is addressed via the Table Pointer register, which is comprised of three Pointer registers:

- TBLPTRU, at RAM address 0FF8h
- TBLPTRH, at RAM address 0FF7h
- TBLPTRL, at RAM address 0FF6h

TBLPTRU	TBLPTRH	TBLPTRL
Addr[21:16]	Addr[15:8]	Addr[7:0]

The 4-bit command, '0000' (core instruction), is used to load the Table Pointer prior to using any read or write operations.

FIGURE 2-10: CONFIGURATION AND ID LOCATIONS FOR PIC18F2XK20/4XK20 DEVICES

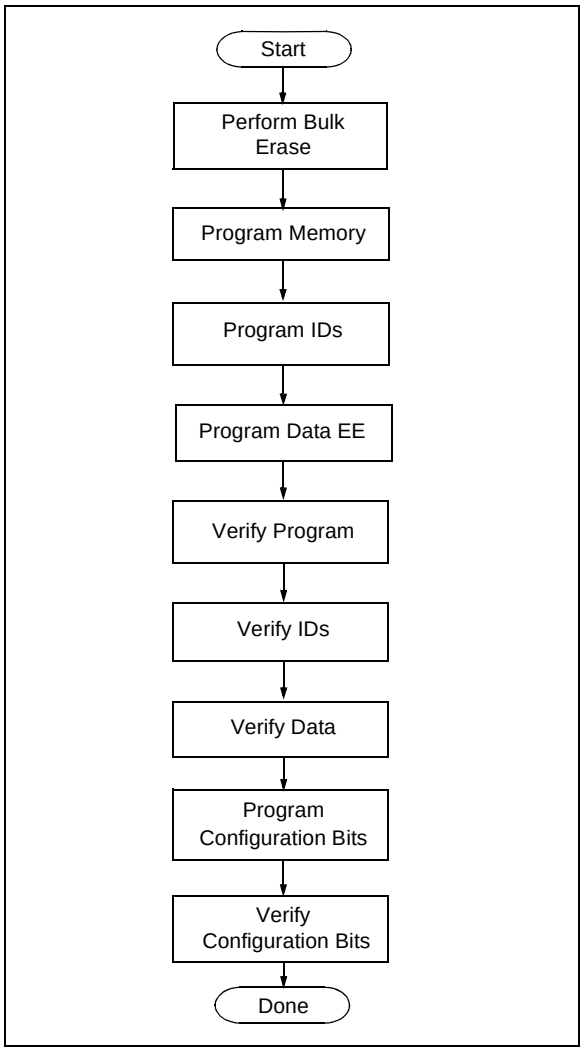


Note: Sizes of memory areas are not to scale.

2.4 High-Level Overview of the Programming Process

Figure 2-11 shows the high-level overview of the programming process. First, a Bulk Erase is performed. Next, the code memory, ID locations and data EEPROM are programmed. These memories are then verified to ensure that programming was successful. If no errors are detected, the Configuration bits are then programmed and verified.

FIGURE 2-11: HIGH-LEVEL PROGRAMMING FLOW



2.5 Entering and Exiting High-Voltage ICSP Program/Verify Mode

As shown in Figure 2-12, the High-Voltage ICSP Program/Verify mode is entered by holding PGC and PGD low and then raising $\overline{MCLR}/V_{PP}$/RE3 to V_{IHH} (high voltage). Once in this mode, the code memory, data EEPROM, ID locations and Configuration bits can be accessed and programmed in serial fashion. Figure 2-13 shows the exit sequence.

The sequence that enters the device into the Program/Verify mode places all unused I/Os in the high-impedance state.

FIGURE 2-12: ENTERING HIGH-VOLTAGE PROGRAM/VERIFY MODE

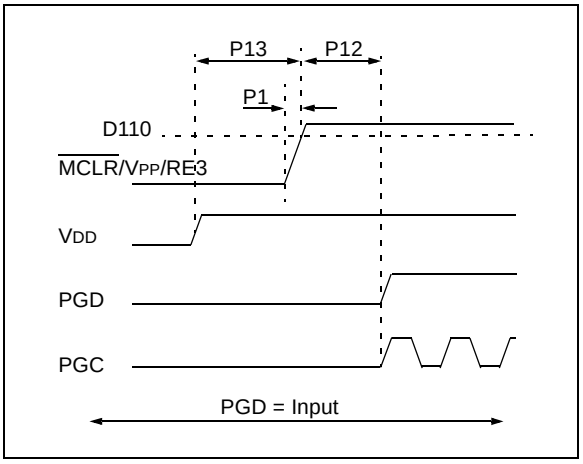


FIGURE 2-13: EXITING HIGH-VOLTAGE PROGRAM/VERIFY MODE

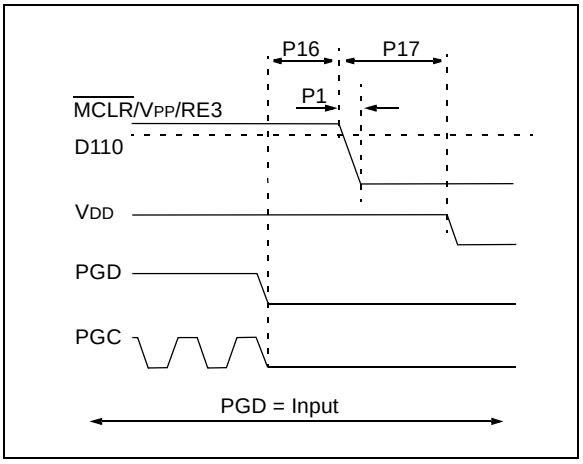


TABLE 2-7: SAMPLE COMMAND SEQUENCE

4-Bit Command	Data Payload	Core Instruction
1101	3C 40	Table Write, post-increment by 2

FIGURE 2-16: TABLE WRITE, POST-INCREMENT TIMING DIAGRAM (1101)

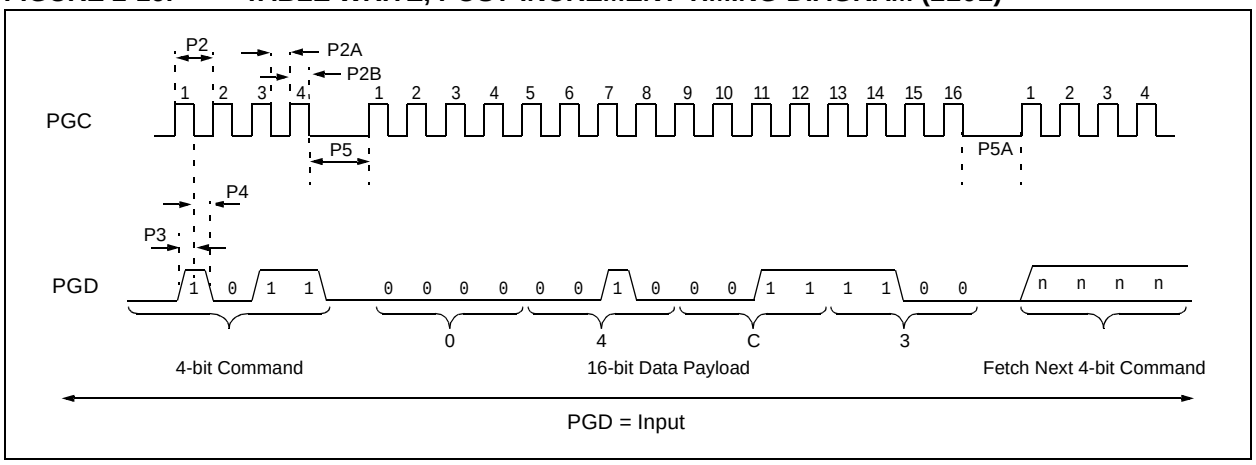
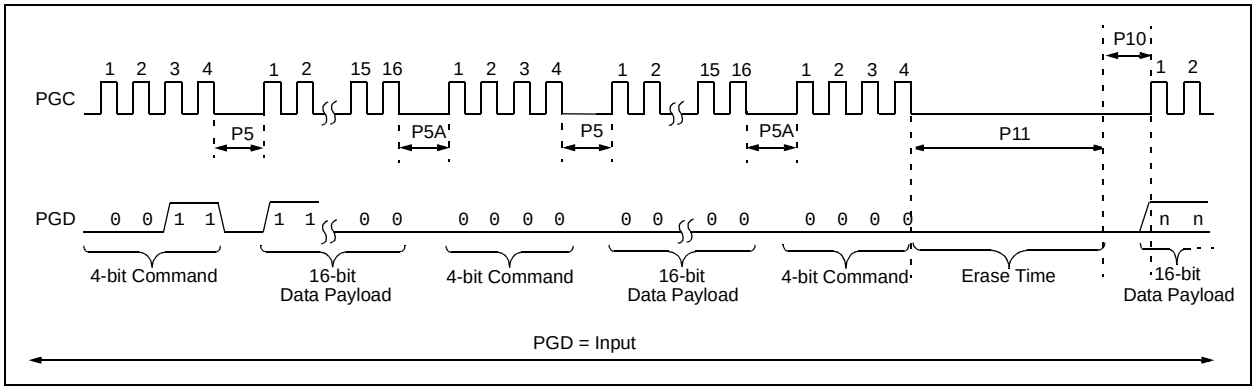


FIGURE 3-2: BULK ERASE TIMING DIAGRAM



3.1.2 LOW-VOLTAGE ICSP BULK ERASE

When using low-voltage ICSP, the part must be supplied by the voltage specified in parameter D111 if a Bulk Erase is to be executed. All other Bulk Erase details as described above apply.

If it is determined that a program memory erase must be performed at a supply voltage below the Bulk Erase limit, refer to the erase methodology described in **Section 3.1.3 "ICSP Row Erase"** and **Section 3.2.1 "Modifying Code Memory"**.

If it is determined that a data EEPROM erase must be performed at a supply voltage below the Bulk Erase limit, follow the methodology described in **Section 3.3 "Data EEPROM Programming"** and write '1's to the array.

3.1.3 ICSP ROW ERASE

Regardless of whether high or low-voltage ICSP is used, it is possible to erase one row (64 bytes of data), provided the block is not code or write-protected. Rows are located at static boundaries beginning at program memory address 000000h, extending to the internal program memory limit (see **Section 2.3 "Memory Maps"**).

The Row Erase duration is self-timed. After the WR bit in EECON1 is set, two NOPs are issued. Erase starts upon the 4th PGC of the second NOP. It ends when the WR bit is cleared by hardware.

The code sequence to Row Erase a PIC18F2XK20/4XK20 device is shown in Table 3-3. The flowchart shown in Figure 3-3 depicts the logic necessary to completely erase a PIC18F2XK20/4XK20 device. The timing diagram for Row Erase is identical to the data EEPROM write timing shown in Figure 3-7.

Note:	The TBLPTR register can point at any byte within the row intended for erase.

TABLE 3-3: ERASE CODE MEMORY CODE SEQUENCE

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to code memory and enable writes.		
0000	8E A6	BSF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
0000	84 A6	BSF EECON1, WREN
Step 2: Point to first row in code memory.		
0000	6A F8	CLRF TBLPTRU
0000	6A F7	CLRF TBLPTRH
0000	6A F6	CLRF TBLPTRL
Step 3: Enable erase and erase single row.		
0000	88 A6	BSF EECON1, FREE
0000	82 A6	BSF EECON1, WR
0000	00 00	NOP
0000	00 00	NOP Erase starts on the 4th clock of this instruction
Step 4: Poll WR bit. Repeat until bit is clear.		
0000	50 A6	MOVF EECON1, W, 0
0000	6E F5	MOVWF TABLAT
0000	00 00	NOP
0010	<MSB><LSB>	Shift out data(1)
Step 5: Hold PGC low for time P10.		
Step 6: Repeat step 3 with Address Pointer incremented by 64 until all rows are erased.		
Step 7: Disable writes.		
0000	94 A6	BCF EECON1, WREN

Note 1: See Figure 4-4 for details on shift out data timing.

3.2 Code Memory Programming

Programming code memory is accomplished by first loading data into the write buffer and then initiating a programming sequence. The write and erase buffer sizes shown in Table 3-4 can be mapped to any location of the same size beginning at 000000h. The actual memory write sequence takes the contents of this buffer and programs the proper amount of code memory that contains the Table Pointer.

The programming duration is externally timed and is controlled by PGC. After a Start Programming command is issued (4-bit command, '1111'), a NOP is issued, where the 4th PGC is held high for the duration of the programming time, P9.

After PGC is brought low, the programming sequence is terminated. PGC must be held low for the time specified by parameter P10 to allow high-voltage discharge of the memory array.

The code sequence to program a PIC18F2XK20/4XK20 device is shown in Table 3-5. The flowchart shown in Figure 3-4 depicts the logic necessary to completely write a PIC18F2XK20/4XK20 device. The timing diagram that details the Start Programming command and parameters P9 and P10 is shown in Figure 3-5.

Note:	The TBLPTR register must point to the same region when initiating the programming sequence as it did when the write buffers were loaded.

TABLE 3-4: WRITE AND ERASE BUFFER SIZES

Devices (Arranged by Family)	Write Buffer Size (bytes)	Erase Size (bytes)
PIC18F26K20, PIC18F46K20	64	64
PIC18F24K20, PIC18F25K20, PIC18F44K20, PIC18F45K20	32	64
PIC18F23K20, PIC18F43K20	16	64

TABLE 3-5: WRITE CODE MEMORY CODE SEQUENCE

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to code memory.		
0000 0000 0000	8E A6 9C A6 84 A6	BSF EECON1, EEPGD BCF EECON1, CFGS BSF EECON1, WREN
Step 2: Point to row to write.		
0000 0000 0000 0000 0000 0000	0E <Addr[21:16]> 6E F8 0E <Addr[15:8]> 6E F7 0E <Addr[7:0]> 6E F6	MOVLW <Addr[21:16]> MOVWF TBLPTRU MOVLW <Addr[15:8]> MOVWF TBLPTRH MOVLW <Addr[7:0]> MOVWF TBLPTRL
Step 3: Load write buffer. Repeat for all but the last two bytes.		
1101	<MSB><LSB>	Write 2 bytes and post-increment address by 2.
Step 4: Load write buffer for last two bytes and start programming.		
1111 0000	<MSB><LSB> 00 00	Write 2 bytes and start programming. NOP - hold PGC high for time P9 and low for time P10.
To continue writing data, repeat steps 2 through 4, where the Address Pointer is incremented by 2 at each iteration of the loop.		

FIGURE 3-4: PROGRAM CODE MEMORY FLOW

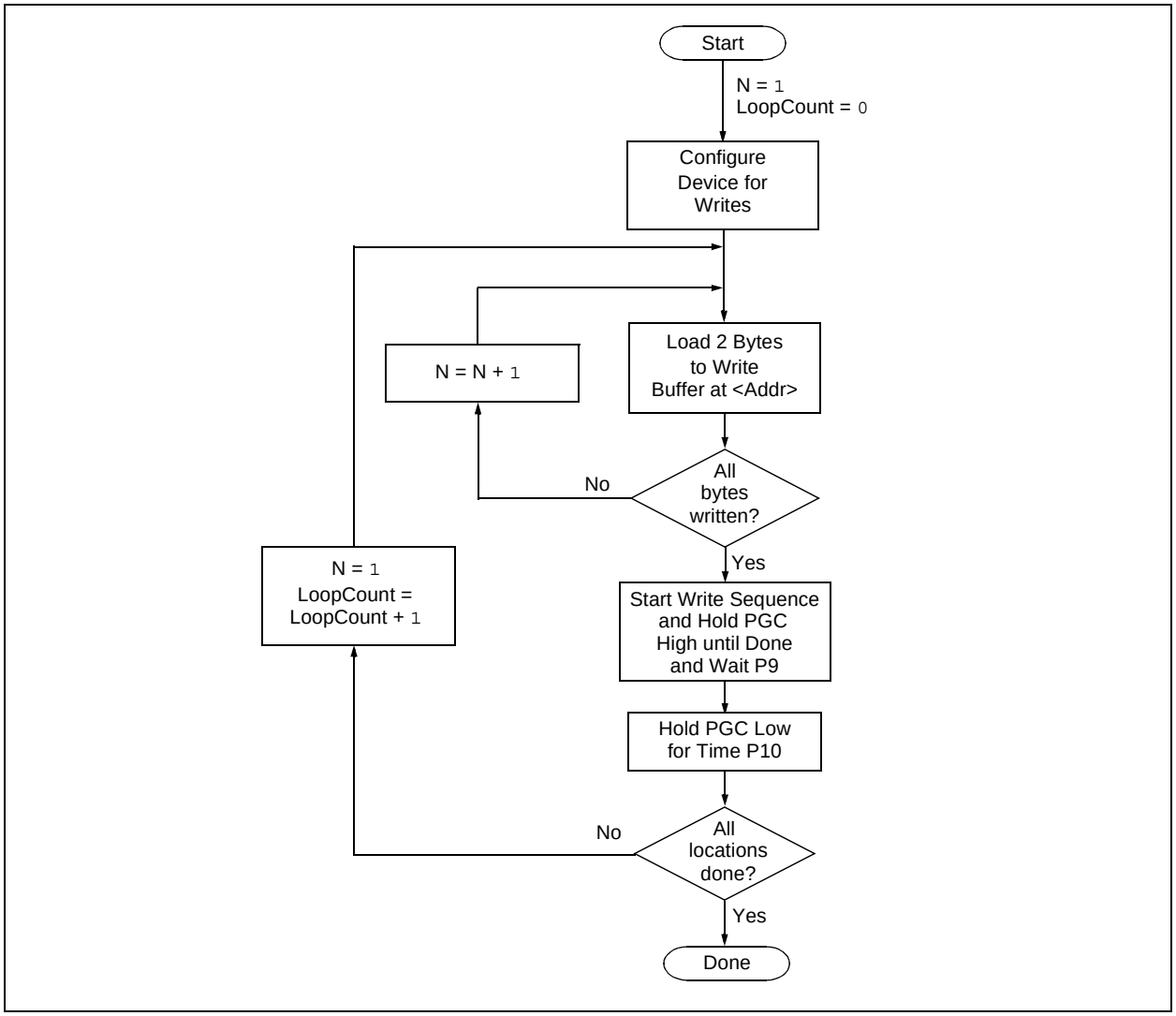
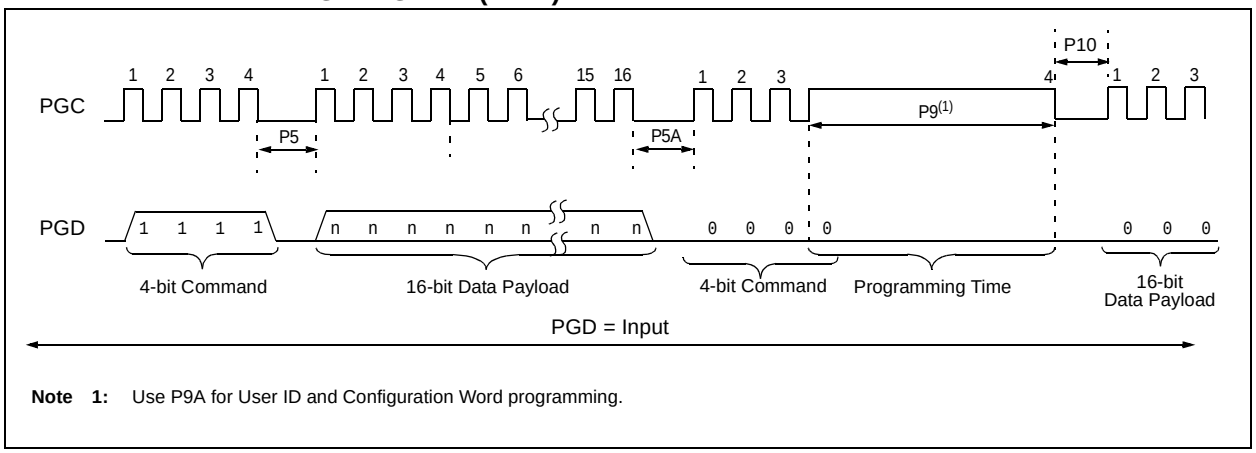


FIGURE 3-5: TABLE WRITE AND START PROGRAMMING INSTRUCTION TIMING DIAGRAM (1111)



Note 1: Use P9A for User ID and Configuration Word programming.

3.2.1 MODIFYING CODE MEMORY

The previous programming example assumed that the device has been Bulk Erased prior to programming (see **Section 3.1.1 "High-Voltage ICSP Bulk Erase"**). It may be the case, however, that the user wishes to modify only a section of an already programmed device.

The appropriate number of bytes required for the erase buffer must be read out of code memory (as described in **Section 4.2 "Verify Code Memory and ID Locations"**) and buffered. Modifications can be made on this buffer. Then, the block of code memory that was read out must be erased and rewritten with the modified data.

The WREN bit must be set if the WR bit in EECON1 is used to initiate a write sequence.

TABLE 3-6: MODIFYING CODE MEMORY

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to code memory.		
0000	8E A6	BSF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
Step 2: Read code memory into buffer (**Section 4.1 "Read Code Memory, ID Locations and Configuration Bits"**).		
Step 3: Set the Table Pointer for the block to be erased.		
0000	0E <Addr[21:16]>	MOVLW <Addr[21:16]>
0000	6E F8	MOVWF TBLPTRU
0000	0E <Addr[8:15]>	MOVLW <Addr[8:15]>
0000	6E F7	MOVWF TBLPTRH
0000	0E <Addr[7:0]>	MOVLW <Addr[7:0]>
0000	6E F6	MOVWF TBLPTRL
Step 4: Enable memory writes and setup an erase.		
0000	84 A6	BSF EECON1, WREN
0000	88 A6	BSF EECON1, FREE
Step 5: Initiate erase.		
0000	88 A6	BSF EECON1, FREE
0000	82 A6	BSF EECON1, WR
0000	00 00	NOP
0000	00 00	NOP Erase starts on the 4th clock of this instruction
Step 6: Poll WR bit. Repeat until bit is clear.		
0000	50 A6	MOVF EECON1, W, 0
0000	6E F5	MOVWF TABLAT
0000	00 00	NOP
0000	<MSB><LSB>	Shift out data(1)
Step 7: Load write buffer. The correct bytes will be selected based on the Table Pointer.		
0000	0E <Addr[21:16]>	MOVLW <Addr[21:16]>
0000	6E F8	MOVWF TBLPTRU
0000	0E <Addr[8:15]>	MOVLW <Addr[8:15]>
0000	6E F7	MOVWF TBLPTRH
0000	0E <Addr[7:0]>	MOVLW <Addr[7:0]>
0000	6E F6	MOVWF TBLPTRL
1101	<MSB><LSB>	Write 2 bytes and post-increment address by 2.
•	•	
•	•	Repeat as many times as necessary to fill the write buffer
•	•	Write 2 bytes and start programming.
1111	<MSB><LSB>	NOP - hold PGC high for time P9 and low for time P10.
0000	00 00	
To continue modifying data, repeat Steps 2 through 6, where the Address Pointer is incremented by the appropriate number of bytes (see Table 3-4) at each iteration of the loop. The write cycle must be repeated enough times to completely rewrite the contents of the erase buffer.		
Step 8: Disable writes.		
0000	94 A6	BCF EECON1, WREN

TABLE 3-7: PROGRAMMING DATA MEMORY

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to data EEPROM.		
0000	9E A6	BCF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
Step 2: Set the data EEPROM Address Pointer.		
0000	0E <Addr>	MOVLW <Addr>
0000	6E A9	MOVWF EEADR
0000	OE <AddrH>	MOVLW <AddrH>
0000	6E AA	MOVWF EEADRH
Step 3: Load the data to be written.		
0000	0E <Data>	MOVLW <Data>
0000	6E A8	MOVWF EEDATA
Step 4: Enable memory writes.		
0000	84 A6	BSF EECON1, WREN
Step 5: Initiate write.		
0000	82 A6	BSF EECON1, WR
0000	00 00	NOP
0000	00 00	NOP ;write starts on 4th clock of this instruction
Step 6: Poll WR bit, repeat until the bit is clear.		
0000	50 A6	MOVF EECON1, W, 0
0000	6E F5	MOVWF TABLAT
0000	00 00	NOP
0010	<MSB><LSB>	Shift out data(1)
Step 7: Hold PGC low for time P10.		
Step 8: Disable writes.		
0000	94 A6	BCF EECON1, WREN
Repeat steps 2 through 8 to write more data.		

Note 1: See Figure 4-4 for details on shift out data timing.

3.5 Boot Block Programming

The code sequence detailed in Table 3-5 should be used, except that the address used in “Step 2” will be in the range of 000000h to 0007FFh.

3.6 Configuration Bits Programming

Unlike code memory, the Configuration bits are programmed a byte at a time. The Table Write, Begin Programming 4-bit command (‘1111’) is used, but only 8 bits of the following 16-bit payload will be written. The LSB of the payload will be written to even addresses and the MSB will be written to odd addresses. The code sequence to program two consecutive configuration locations is shown in Table 3-9. See Figure 3-5 for the timing diagram.

Note:	The address must be explicitly written for each byte programmed. The addresses can not be incremented in this mode.

TABLE 3-9: SET ADDRESS POINTER TO CONFIGURATION LOCATION

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to config memory.		
0000	8E A6	BSF EECON1, EEPGD
0000	8C A6	BSF EECON1, CFGS
0000	84 A6	BSF EECON1, WREN
Step 2(1): Set Table Pointer for config byte to be written. Write even/odd addresses.		
0000	0E 30	MOVLW 30h
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPRTH
0000	0E 00	MOVLW 00h
0000	6E F6	MOVWF TBLPTRL
1111	<MSB ignored><LSB>	Load 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9 and low for time P10.
0000	0E 01	MOVLW 01h
0000	6E F6	MOVWF TBLPTRL
1111	<MSB><LSB ignored>	Load 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9A and low for time P10.

Note 1: Enabling the write protection of Configuration bits (WRTC = 0 in CONFIG6H) will prevent further writing of Configuration bits. Always write all the Configuration bits before enabling the write protection for Configuration bits.

FIGURE 3-8: CONFIGURATION PROGRAMMING FLOW

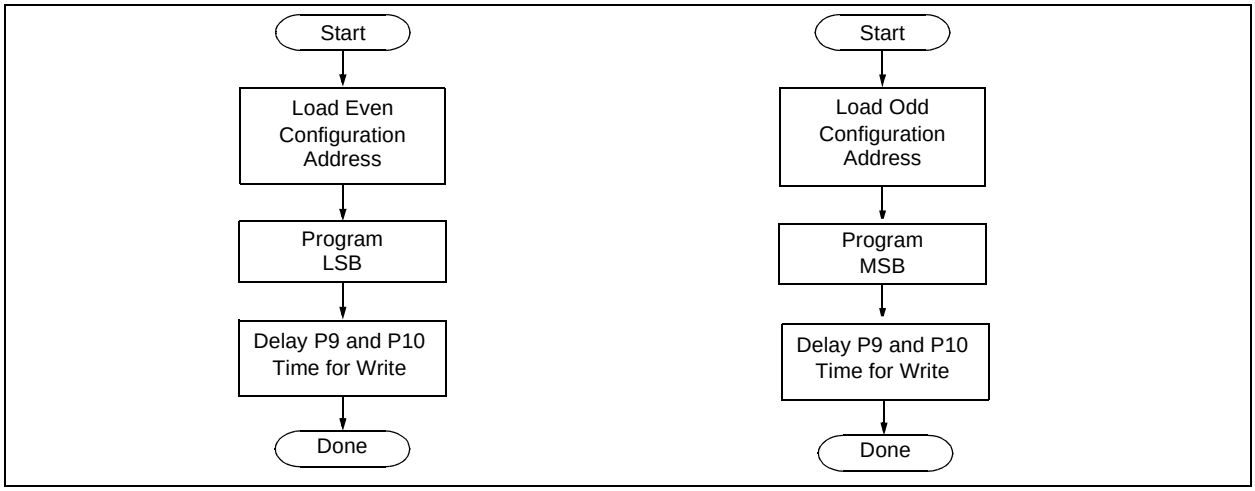


TABLE 5-3: PIC18F2XK20/4XK20 BIT DESCRIPTIONS (CONTINUED)

Bit Name	Configuration Words	Description
WDTEN	CONFIG2H	Watchdog Timer Enable bit 1 = WDT enabled 0 = WDT disabled (control is placed on SWDTEN bit)
MCLRE	CONFIG3H	$\overline{\text{MCLR}}$ Pin Enable bit 1 = $\overline{\text{MCLR}}$ pin enabled, RE3 input pin disabled 0 = RE3 input pin enabled, $\overline{\text{MCLR}}$ pin disabled
HFOFST	CONFIG3H	HFINTOSC Fast Start 1 = HFINTOSC output is not delayed 0 = HFINTOSC output is delayed until oscillator is stable (IOFS = 1)
LPT1OSC	CONFIG3H	Low-Power Timer1 Oscillator Enable bit 1 = Timer1 configured for low-power operation 0 = Timer1 configured for higher power operation
PBADEN	CONFIG3H	PORTB A/D Enable bit 1 = PORTB A/D<4:0> pins are configured as analog input channels on Reset 0 = PORTB A/D<4:0> pins are configured as digital I/O on Reset
CCP2MX	CONFIG3H	CCP2 MUX bit 1 = CCP2 input/output is multiplexed with RC1 0 = CCP2 input/output is multiplexed with RB3
DEBUG	CONFIG4L	Background Debugger Enable bit 1 = Background debugger disabled, RB6 and RB7 configured as general purpose I/O pins 0 = Background debugger enabled, RB6 and RB7 are dedicated to In-Circuit Debug
XINST	CONFIG4L	Extended Instruction Set Enable bit 1 = Instruction set extension and Indexed Addressing mode enabled 0 = Instruction set extension and Indexed Addressing mode disabled (Legacy mode)
LVP	CONFIG4L	Low-Voltage Programming Enable bit 1 = Low-Voltage Programming enabled, RB5 is the PGM pin 0 = Low-Voltage Programming disabled, RB5 is an I/O pin
STVREN	CONFIG4L	Stack Overflow/Underflow Reset Enable bit 1 = Reset on stack overflow/underflow enabled 0 = Reset on stack overflow/underflow disabled

.

TABLE 5-3: PIC18F2XK20/4XK20 BIT DESCRIPTIONS (CONTINUED)

Bit Name	Configuration Words	Description
CP3	CONFIG5L	Code Protection bits (Block 3 code memory area) 1 = Block 3 is not code-protected 0 = Block 3 is code-protected
CP2	CONFIG5L	Code Protection bits (Block 2 code memory area) 1 = Block 2 is not code-protected 0 = Block 2 is code-protected
CP1	CONFIG5L	Code Protection bits (Block 1 code memory area) 1 = Block 1 is not code-protected 0 = Block 1 is code-protected
CP0	CONFIG5L	Code Protection bits (Block 0 code memory area) 1 = Block 0 is not code-protected 0 = Block 0 is code-protected
CPD	CONFIG5H	Code Protection bits (Data EEPROM) 1 = Data EEPROM is not code-protected 0 = Data EEPROM is code-protected
CPB	CONFIG5H	Code Protection bits (Boot Block memory area) 1 = Boot Block is not code-protected 0 = Boot Block is code-protected
WRT3	CONFIG6L	Write Protection bits (Block 3 code memory area) 1 = Block 3 is not write-protected 0 = Block 3 is write-protected
WRT2	CONFIG6L	Write Protection bits (Block 2 code memory area) 1 = Block 2 is not write-protected 0 = Block 2 is write-protected
WRT1	CONFIG6L	Write Protection bits (Block 1 code memory area) 1 = Block 1 is not write-protected 0 = Block 1 is write-protected
WRT0	CONFIG6L	Write Protection bits (Block 0 code memory area) 1 = Block 0 is not write-protected 0 = Block 0 is write-protected
WRTD	CONFIG6H	Write Protection bit (Data EEPROM) 1 = Data EEPROM is not write-protected 0 = Data EEPROM is write-protected
WRTB	CONFIG6H	Write Protection bit (Boot Block memory area) 1 = Boot Block is not write-protected 0 = Boot Block is write-protected
WRTC	CONFIG6H	Write Protection bit (Configuration registers) 1 = Configuration registers are not write-protected 0 = Configuration registers are write-protected

.

TABLE 5-3: PIC18F2XK20/4XK20 BIT DESCRIPTIONS (CONTINUED)

Bit Name	Configuration Words	Description
EBTR3	CONFIG7L	Table Read Protection bit (Block 3 code memory area) 1 = Block 3 is not protected from table reads executed in other blocks 0 = Block 3 is protected from table reads executed in other blocks
EBTR2	CONFIG7L	Table Read Protection bit (Block 2 code memory area) 1 = Block 2 is not protected from table reads executed in other blocks 0 = Block 2 is protected from table reads executed in other blocks
EBTR1	CONFIG7L	Table Read Protection bit (Block 1 code memory area) 1 = Block 1 is not protected from table reads executed in other blocks 0 = Block 1 is protected from table reads executed in other blocks
EBTR0	CONFIG7L	Table Read Protection bit (Block 0 code memory area) 1 = Block 0 is not protected from table reads executed in other blocks 0 = Block 0 is protected from table reads executed in other blocks
EBTRB	CONFIG7H	Table Read Protection bit (Boot Block memory area) 1 = Boot Block is not protected from table reads executed in other blocks 0 = Boot Block is protected from table reads executed in other blocks
DEV<10:3>	DEVID2	Device ID bits These bits are used with the DEV<2:0> bits in the DEVID1 register to identify part number.
DEV<2:0>	DEVID1	Device ID bits These bits are used with the DEV<10:3> bits in the DEVID2 register to identify part number.
REV<4:0>	DEVID1	Revision ID bits These bits are used to indicate the revision of the device.

.

5.3 Single-Supply ICSP Programming

The LVP bit in Configuration register, CONFIG4L, enables Single-Supply (Low-Voltage) ICSP Programming. The LVP bit defaults to a '1' (enabled) from the factory.

If Single-Supply Programming mode is not used, the LVP bit can be programmed to a '0' and RB5/PGM becomes a digital I/O pin. However, the LVP bit may only be programmed by entering the High-Voltage ICSP mode, where MCLR/VPP/RE3 is raised to VIHH. Once the LVP bit is programmed to a '0', only the High-Voltage ICSP mode is available and only the High-Voltage ICSP mode can be used to program the device.

Note 1: The High-Voltage ICSP mode is always available, regardless of the state of the LVP bit, by applying VIHH to the MCLR/VPP/RE3 pin.

2: While in Low-Voltage ICSP mode, the RB5 pin can no longer be used as a general purpose I/O.

5.4 Embedding Configuration Word Information in the HEX File

To allow portability of code, a PIC18F2XK20/4XK20 programmer is required to read the Configuration Word locations from the hex file. If Configuration Word information is not present in the hex file, then a simple warning message should be issued. Similarly, while saving a hex file, all Configuration Word information must be included. An option to not include the Configuration Word information may be provided. When embedding Configuration Word information in the hex file, it should start at address 300000h.

Microchip Technology Inc. feels strongly that this feature is important for the benefit of the end customer.

5.5 Embedding Data EEPROM Information In the HEX File

To allow portability of code, a PIC18F2XK20/4XK20 programmer is required to read the data EEPROM information from the hex file. If data EEPROM information is not present, a simple warning message should be issued. Similarly, when saving a hex file, all data EEPROM information must be included. An option to not include the data EEPROM information may be provided. When embedding data EEPROM information in the hex file, it should start at address F00000h.

Microchip Technology Inc. believes that this feature is important for the benefit of the end customer.

5.6 Checksum Computation

The checksum is calculated by summing the following:

- The contents of all code memory locations
- The Configuration Word, appropriately masked
- ID locations (Only if any portion of program memory is code-protected)

The Least Significant 16 bits of this sum are the checksum.

Code protection limits access to program memory by both external programmer (code-protect) and code execution (table read protect). The ID locations, when included in a code protected checksum, contain the checksum of an unprotected part. The unprotected checksum is distributed: one nibble per ID location. Each nibble is right justified.

Table 5-4 describes how to calculate the checksum for each device.

Note: The checksum calculation differs depending on the code-protect setting. Since the code memory locations read out differently depending on the code-protect setting, the table describes how to manipulate the actual code memory values to simulate the values that would be read from a protected device. When calculating a checksum by reading a device, the entire code memory can simply be read and summed. The Configuration Word and ID locations can always be read.

TABLE 5-4: CHECKSUM COMPUTATION

Device	Code-Protect	Checksum	Blank Value	0xAA at 0 and Max Address
PIC18FX3K20	None	SUM[0000:01FF]+SUM[0200:0FFF]+SUM[1000:1FFF]+ (CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)	E33Eh	E294h
	Boot Block	SUM[0200:0FFF]+SUM[1000:1FFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 03h)+(CONFIG5H & C0h)+ (CONFIG6L & 03h)+(CONFIG6H & E0h)+(CONFIG7L & 03h)+ (CONFIG7H & 40h)+SUM_ID	E520h	E4C6h
	Boot/ Block 0	SUM[1000:1FFF]+(CONFIG1L & 00h)+(CONFIG1H & CFh)+ (CONFIG2L & 1Fh)+(CONFIG2H & 1F)+(CONFIG3L & 00h)+ (CONFIG3H & 8Fh)+(CONFIG4L & C5h)+(CONFIG4H & 00h)+ (CONFIG5L & 03h)+(CONFIG5H & C0h)+(CONFIG6L & 03h)+ (CONFIG6H & E0h)+(CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	F31Fh	F2C5h
	All	(CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	031Dh	0318h
PIC18FX4K20	None	SUM[0000:07FF]+SUM[0800:1FFF]+SUM[2000:3FFF]+ (CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)	C33Eh	C294h
	Boot Block	SUM[0800:1FFF]+SUM[2000:3FFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 03h)+(CONFIG5H & C0h)+ (CONFIG6L & 03h)+(CONFIG6H & E0h)+(CONFIG7L & 03h)+ (CONFIG7H & 40h)+SUM_ID	CB1Eh	CAC4h
	Boot/ Block 0	SUM[2000:3FFF]+(CONFIG1L & 00h)+(CONFIG1H & CFh)+ (CONFIG2L & 1Fh)+(CONFIG2H & 1F)+(CONFIG3L & 00h)+ (CONFIG3H & 8Fh)+(CONFIG4L & C5h)+(CONFIG4H & 00h)+ (CONFIG5L & 03h)+(CONFIG5H & C0h)+(CONFIG6L & 03h)+ (CONFIG6H & E0h)+(CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	E31Dh	E2C3h
	All	(CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	031Bh	0316h

Legend:

Item		Description
CONFIGx	=	Configuration Word
SUM[a:b]	=	Sum of locations, a to b inclusive
SUM_ID	=	Byte-wise sum of lower four bits of all customer ID locations
+	=	Addition
&	=	Bit-wise AND

TABLE 5-4: CHECKSUM COMPUTATION (CONTINUED)

Device	Code-Protect	Checksum	Blank Value	0xAA at 0 and Max Address
PIC18FX5K20	None	SUM[0000:07FF]+SUM[0800:1FFF]+SUM[2000:3FFF]+ SUM[4000:5FFF]+SUM[6000:7FFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 0Fh)+(CONFIG5H & C0h)+ (CONFIG6L & 0Fh)+(CONFIG6H & E0h)+(CONFIG7L & 0Fh)+ (CONFIG7H & 40h)	8362h	82B8h
	Boot Block	SUM[0800:1FFF]+SUM[2000:3FFF]+SUM[4000:5FFF]+SUM[6000:7FFF]+ (CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 0Fh)+ (CONFIG5H & C0h)+(CONFIG6L & 0Fh)+(CONFIG6H & E0h)+ (CONFIG7L & 0Fh)+(CONFIG7H & 40h)+SUM_ID	8B35h	8AEAh
	Boot/ Block 0/ Block 1	SUM[4000:5FFF]+SUM[6000:7FFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 0Fh)+(CONFIG5H & C0h)+ (CONFIG6L & 0Fh)+(CONFIG6H & E0h)+(CONFIG7L & 0Fh)+ (CONFIG7H & 40h)+SUM_ID	C332h	C2E7h
	All	(CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 0Fh)+ (CONFIG5H & C0h)+(CONFIG6L & 0Fh)+(CONFIG6H & E0h)+ (CONFIG7L & 0Fh)+(CONFIG7H & 40h)+SUM_ID	0326h	0330h

Legend:

Item		Description
CONFIGx	=	Configuration Word
SUM[a:b]	=	Sum of locations, a to b inclusive
SUM_ID	=	Byte-wise sum of lower four bits of all customer ID locations
+	=	Addition
&	=	Bit-wise AND

TABLE 5-4: CHECKSUM COMPUTATION (CONTINUED)

Device	Code-Protect	Checksum	Blank Value	0xAA at 0 and Max Address
PIC18FX6K20	None	SUM[0000:07FF]+SUM[0800:3FFF]+SUM[4000:7FFF]+ SUM[8000:BFFF]+SUM[C000:FFFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 0Fh)+(CONFIG5H & C0h)+ (CONFIG6L & 0Fh)+(CONFIG6H & E0h)+(CONFIG7L & 0Fh)+ (CONFIG7H & 40h)	0362h	02B8h
	Boot Block	SUM[0800:3FFF]+SUM[4000:7FFF]+SUM[8000:BFFF]+SUM[C000:FFFF]+ (CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 0Fh)+ (CONFIG5H & C0h)+(CONFIG6L & 0Fh)+(CONFIG6H & E0h)+ (CONFIG7L & 0Fh)+(CONFIG7H & 40h)+SUM_ID	0B2Dh	0AE2h
	Boot/ Block 0/ Block 1	SUM[3000:BFFF]+SUM[C000:FFFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 0Fh)+(CONFIG5H & C0h)+ (CONFIG6L & 0Fh)+(CONFIG6H & E0h)+(CONFIG7L & 0Fh)+ (CONFIG7H & 40h)+SUM_ID	832Ah	82DFh
	All	(CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 0Fh)+ (CONFIG5H & C0h)+(CONFIG6L & 0Fh)+(CONFIG6H & E0h)+ (CONFIG7L & 0Fh)+(CONFIG7H & 40h)+SUM_ID	031Eh	0328h

Legend:

Item		Description
CONFIGx	=	Configuration Word
SUM[a:b]	=	Sum of locations, a to b inclusive
SUM_ID	=	Byte-wise sum of lower four bits of all customer ID locations
+	=	Addition
&	=	Bit-wise AND

6.0 AC/DC CHARACTERISTICS TIMING REQUIREMENTS FOR PROGRAM/ VERIFY TEST MODE

Standard Operating Conditions
Operating Temperature: 25°C is recommended

Param No.	Sym.	Characteristic	Min.	Max.	Units	Conditions
D110	VIHH	High-Voltage Programming Voltage on MCLR/VPP/RE3	VDD + 4.5	9	V	
D110A	VIHL	Low-Voltage Programming Voltage on MCLR/VPP/RE3	1.80	3.60	V	
D111	VDD	Supply Voltage During Programming	1.80	3.60	V	Row Erase/Write
			2.7	3.60	V	Bulk Erase operations
D112	IPP	Programming Current on MCLR/VPP/RE3	—	300	μA	
D113	IDDP	Supply Current During Programming	—	10	mA	
D031	VIL	Input Low Voltage	VSS	0.2 VDD	V	
D041	VIH	Input High Voltage	0.8 VDD	VDD	V	
D080	VOL	Output Low Voltage	—	0.6	V	IOL = X.X mA @ 2.7V
D090	VOH	Output High Voltage	VDD – 0.7	—	V	IOH = -Y.Y mA @ 2.7V
D012	CIO	Capacitive Loading on I/O pin (PGD)	—	50	pF	To meet AC specifications
P1	TR	MCLR/VPP/RE3 Rise Time to enter Program/Verify mode	—	1.0	μs	**(Note 1)**
P2	TPGC	Serial Clock (PGC) Period	100	—	ns	VDD = 3.6V
			1	—	μs	VDD = 1.8V
P2A	TPGCL	Serial Clock (PGC) Low Time	40	—	ns	VDD = 3.6V
			400	—	ns	VDD = 1.8V
P2B	TPGCH	Serial Clock (PGC) High Time	40	—	ns	VDD = 3.6V
			400	—	ns	VDD = 1.8V
P3	TSET1	Input Data Setup Time to Serial Clock ↓	15	—	ns	
P4	THLD1	Input Data Hold Time from PGC ↓	15	—	ns	
P5	TDLY1	Delay between 4-bit Command and Command Operand	40	—	ns	
P5A	TDLY1A	Delay between 4-bit Command Operand and next 4-bit Command	40	—	ns	
P6	TDLY2	Delay between Last PGC ↓ of Command Byte to First PGC ↑ of Read of Data Word	20	—	ns	
P9	TDLY5	PGC High Time (minimum programming time)	1	—	ms	Externally Timed
P9A	TDLY5A	PGC High Time	5		ms	Configuration Word programming time
P10	TDLY6	PGC Low Time after Programming (high-voltage discharge time)	200	—	μs	
P11	TDLY7	Delay to allow Self-Timed Data Write or Bulk Erase to occur	5	—	ms	
P11A	TDRWT	Data Write Polling Time	4	—	ms	

Note 1: Do not allow excess time when transitioning MCLR between VIL and VIHH; this can cause spurious program executions to occur. The maximum transition time is:
1 TCY + TPWRT (if enabled) + 1024 TOSC (for LP, HS, HS/PLL and XT modes only) + 2 ms (for HS/PLL mode only) + 1.5 μs (for EC mode only) where TCY is the instruction cycle time, TPWRT is the Power-up Timer period and TOSC is the oscillator period. For specific values, refer to the Electrical Characteristics section of the device data sheet for the particular device.

6.0 AC/DC CHARACTERISTICS TIMING REQUIREMENTS FOR PROGRAM/ VERIFY TEST MODE (CONTINUED)

Standard Operating Conditions
Operating Temperature: 25°C is recommended

Param No.	Sym.	Characteristic	Min.	Max.	Units	Conditions
P12	THLD2	Input Data Hold Time from $\overline{MCLR}$/VPP/RE3 ↑	2	—	µs	
P13	TSET2	VDD ↑ Setup Time to $\overline{MCLR}$/VPP/RE3 ↑	100	—	ns	
P14	TVALID	Data Out Valid from PGC ↑	10	—	ns	
P15	TSET3	PGM ↑ Setup Time to $\overline{MCLR}$/VPP/RE3 ↑	2	—	µs	
P16	TDLY8	Delay between Last PGC ↓ and $\overline{MCLR}$/VPP/RE3 ↓	0	—	s	
P17	THLD3	$\overline{MCLR}$/VPP/RE3 ↓ to VDD ↓	—	100	ns	
P18	THLD4	$\overline{MCLR}$/VPP/RE3 ↓ to PGM ↓	0	—	s	
P19	THIZ	Delay from PGC ↑ to PGD High-Z	3	10	nS	
P20	TPPDP	Hold time after VPP changes	5	—	µs	

Note 1: Do not allow excess time when transitioning $\overline{MCLR}$ between VIL and VIHH; this can cause spurious program executions to occur. The maximum transition time is:
1 TCY + TPWRT (if enabled) + 1024 TOSC (for LP, HS, HS/PLL and XT modes only) + 2 ms (for HS/PLL mode only) + 1.5 µs (for EC mode only) where TCY is the instruction cycle time, TPWRT is the Power-up Timer period and TOSC is the oscillator period. For specific values, refer to the Electrical Characteristics section of the device data sheet for the particular device.